

Cont'd  
B1  
H<sub>2</sub> to said insulating layer, said silicon-containing structure and said conductive structure, such that the reaction between said O<sub>2</sub> and H<sub>2</sub> does not increase the pressure in the processing chamber beyond a predetermined level.

B2  
B2-SubC2  
9 (Twice Amended). A method of oxidizing, in a semiconductor processing chamber, a first feature while leaving a second feature substantially unoxidized, said method comprised of subjecting said first and second features to O<sub>2</sub> and H<sub>2</sub>, such that the reaction between said O<sub>2</sub> and H<sub>2</sub> does not increase the pressure in the processing chamber beyond a predetermined level.

B3  
B3-SubC3  
16 (Twice Amended). A method of fabricating, in a semiconductor processing chamber, a capacitor having a dielectric between a bottom electrode and a top electrode and situated over a semiconductor substrate, said method comprising the steps of:  
providing said bottom electrode over said semiconductor substrate;  
providing a dielectric material over said bottom electrode; and  
subjecting said bottom electrode and said dielectric material to O<sub>2</sub> and H<sub>2</sub>, wherein said dielectric material is oxidized and said bottom electrode remains substantially unoxidized, such that the reaction between said O<sub>2</sub> and H<sub>2</sub> does not increase the pressure in the processing chamber beyond a predetermined level.

B4  
B4-SubC4  
20 (Amended). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O<sub>2</sub> and H<sub>2</sub> in a portion of a process chamber's total volume, such that reaction between the O<sub>2</sub> and H<sub>2</sub> occurs continuously as the O<sub>2</sub> and H<sub>2</sub> enter the chamber.

B5  
B5-SubC5  
22 (Amended). The method of claim 9 and further comprising the step of introducing O<sub>2</sub> and H<sub>2</sub> in a portion of a process chamber's total volume, such that

Claim 15  
reaction between the O<sub>2</sub> and H<sub>2</sub> occurs continuously as the O<sub>2</sub> and H<sub>2</sub> enter the chamber.

Sub 6  
24 (Amended). The method of claim 16 and further comprising the step of introducing O<sub>2</sub> and H<sub>2</sub> in a portion of a process chamber's total volume, such that reaction between the O<sub>2</sub> and H<sub>2</sub> occurs continuously as the O<sub>2</sub> and H<sub>2</sub> enter the chamber.

Sub 7  
26 (Amended). A method of fabricating an electrical device formed in a semiconductor substrate, said method comprising:  
forming an insulating layer over said semiconductor substrate;  
forming a silicon-containing structure on said insulating layer;  
forming a conductive structure on said silicon-containing structure; and  
oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing an oxygen-containing gas selected from the group consisting of O<sub>2</sub>, N<sub>2</sub>O, CO<sub>2</sub> and a separate hydrogen-containing gas to said insulating layer, said silicon-containing structure and said conductive structure, such that the reaction between said O<sub>2</sub> and H<sub>2</sub> does not increase the pressure in the processing chamber beyond a predetermined level.

27 (Amended). The method of claim 26 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing said oxygen-containing gas and said hydrogen containing gas in a portion of a process chamber's total volume, such that reaction between the O<sub>2</sub> and H<sub>2</sub> occurs continuously as the O<sub>2</sub> and H<sub>2</sub> enter the chamber.

Sub 8  
29 (New). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O<sub>2</sub> and